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(12) **United States Design Patent**  
**Sawada**

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(54) **POWER SEMICONDUCTOR MODULE**

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(73) Assignee: **ROHM CO., LTD.**, Kyoto (JP)

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(51) **LOC (12) Cl.** ..... **13-03**

(52) **U.S. Cl.**  
USPC ..... **D13/182**

(58) **Field of Classification Search**

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361/679.01, 713, 728, 736, 760, 761, 772,  
361/775, 783, 820; 174/250, 253;  
438/15, 25, 26, 51, 55, 63, 64, 106  
CPC . H01L 21/00; H01L 2224/42; H01L 2224/43;  
H01L 2021/00; H01L 2021/02; H01L  
2021/04; H01L 21/4814; H01L 21/4846;  
H01L 21/4871; H01L 21/67144; H01L  
23/12; H01L 23/13; H01L 23/14; H01L  
23/147; H01L 2924/171; H01L  
2924/1711; H01L 2924/1715; H01L  
2924/17151; H01L 2924/181; H01L  
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2924/19042; H01L 2924/1905; H01L  
2224/08054; H01L 23/58; H05B 41/14;  
H02B 6/4201; G02B 6/4256; G02B  
6/4257; G02B 6/4261; G02B 6/4262;  
G02B 6/428; G02B 6/4281; H05K 1/14;  
H05K 1/141; H05K 1/142; H05K 1/144;  
H05K 1/18; H05K 1/181; H05K 1/182;  
H05K 1/026

See application file for complete search history.

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(Continued)

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Mueller & Larson, P.C.

(57) **CLAIM**

The ornamental design for a power semiconductor module,  
as shown and described.

**DESCRIPTION**

FIG. 1 is a front, top, and right side perspective view of a  
first embodiment of a power semiconductor module showing  
my new design;

FIG. 2 is a front view thereof;

FIG. 3 is a rear view thereof;

FIG. 4 is a top plan view thereof;

FIG. 5 is a right side view thereof;

FIG. 6 is a left side view thereof;

FIG. 7 is a front, top, and right side perspective view of a  
second embodiment of a power semiconductor module  
showing my new design;

FIG. 8 is a front view thereof;

FIG. 9 is a rear view thereof;

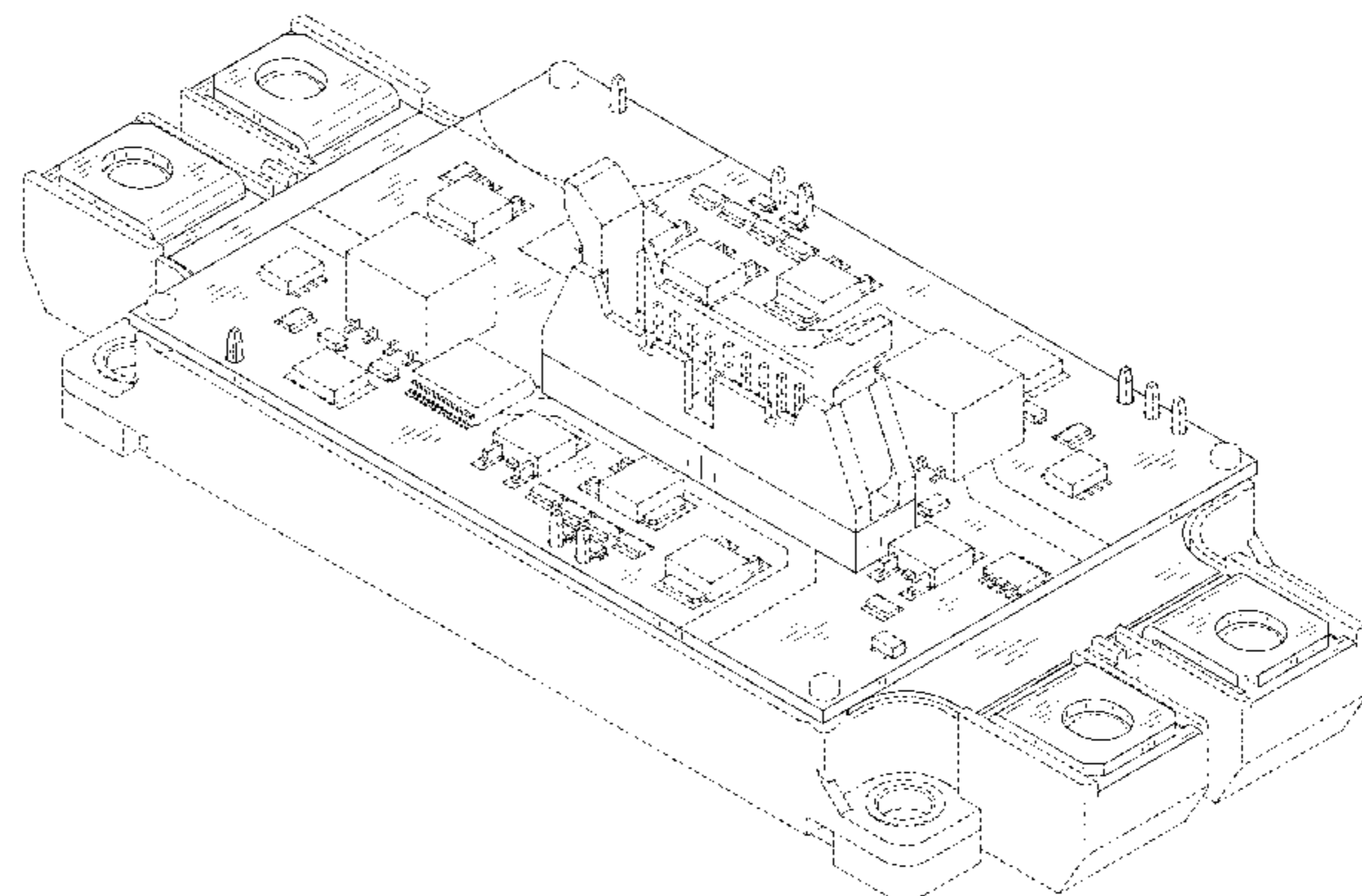
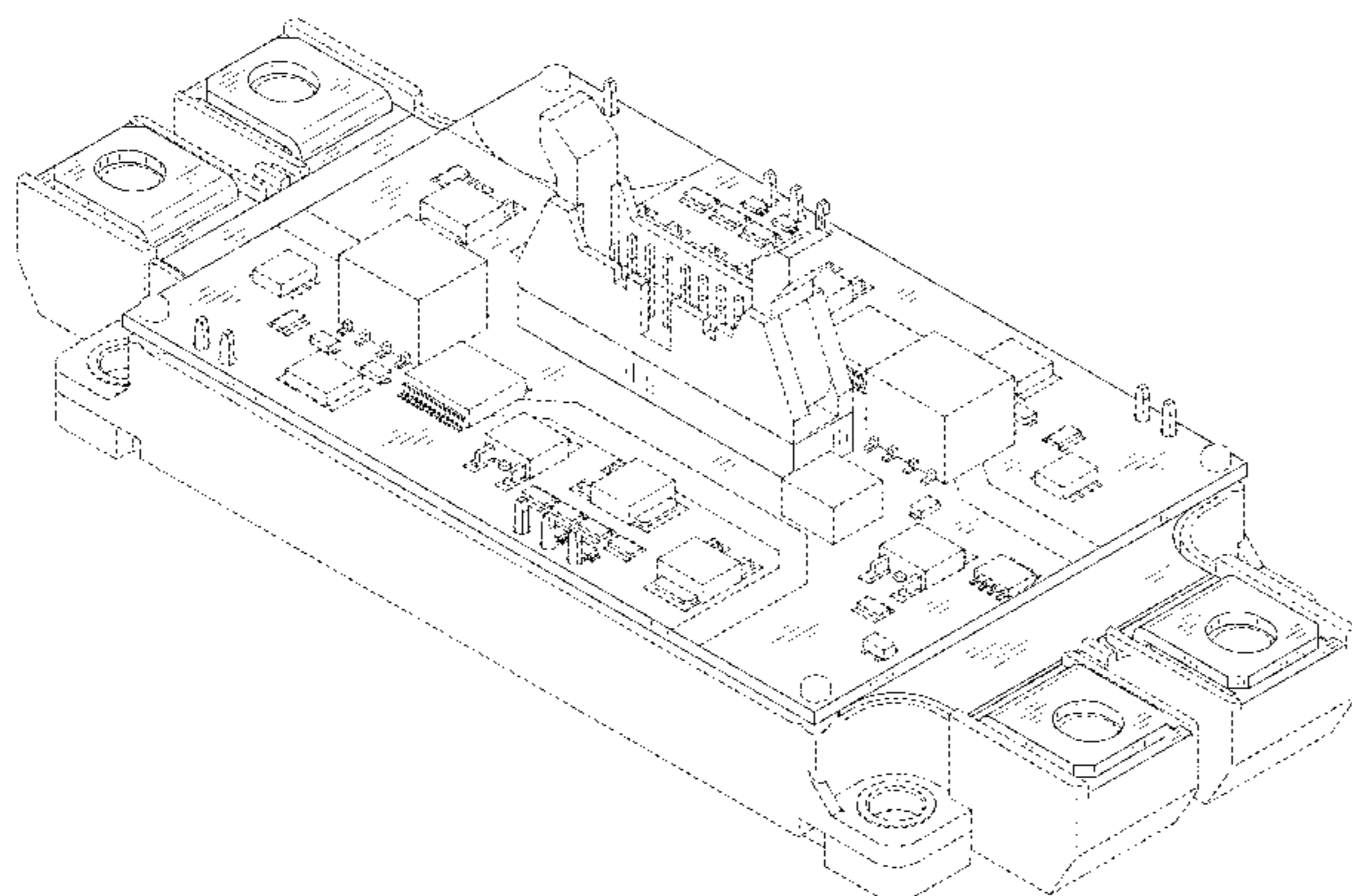
FIG. 10 is a top plan view thereof;

FIG. 11 is a right side view thereof; and,

FIG. 12 is a left side view thereof.

The features shown in broken lines in the drawings depict  
portions of the article that form no part of the claimed  
design. The dash-dotted lines denote the boundary of the  
claim and form no part of the claimed design.

**1 Claim, 12 Drawing Sheets**



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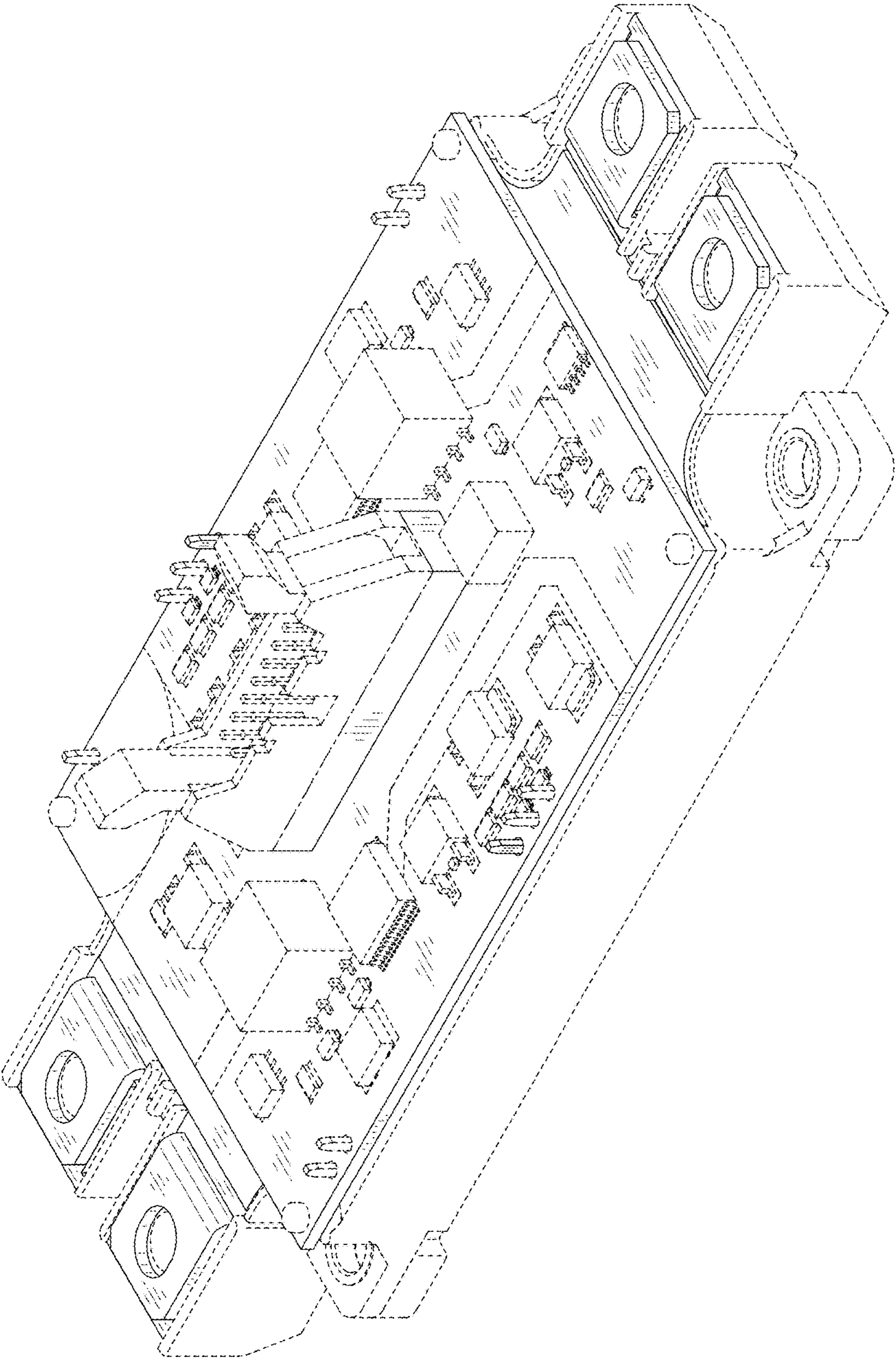


FIG.1

FIG.2

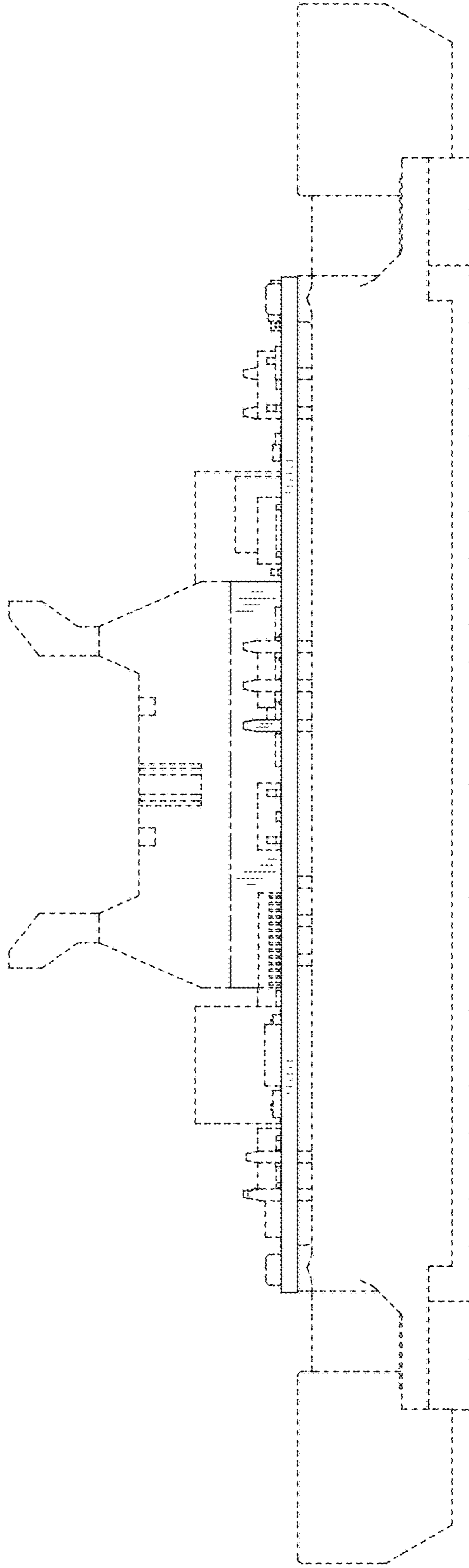
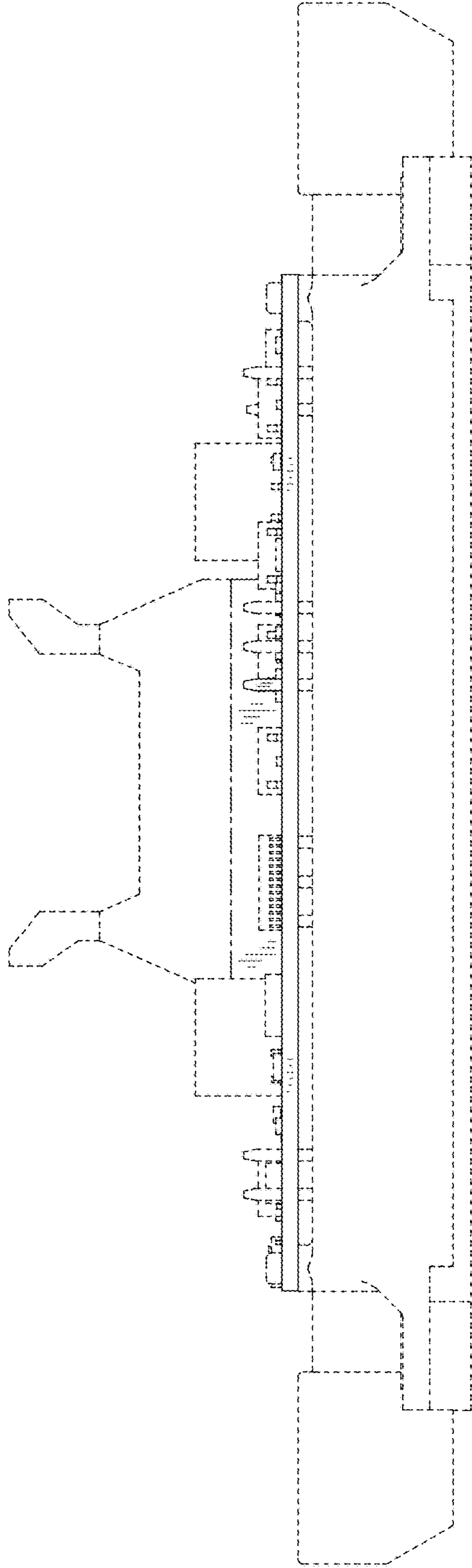


FIG.3



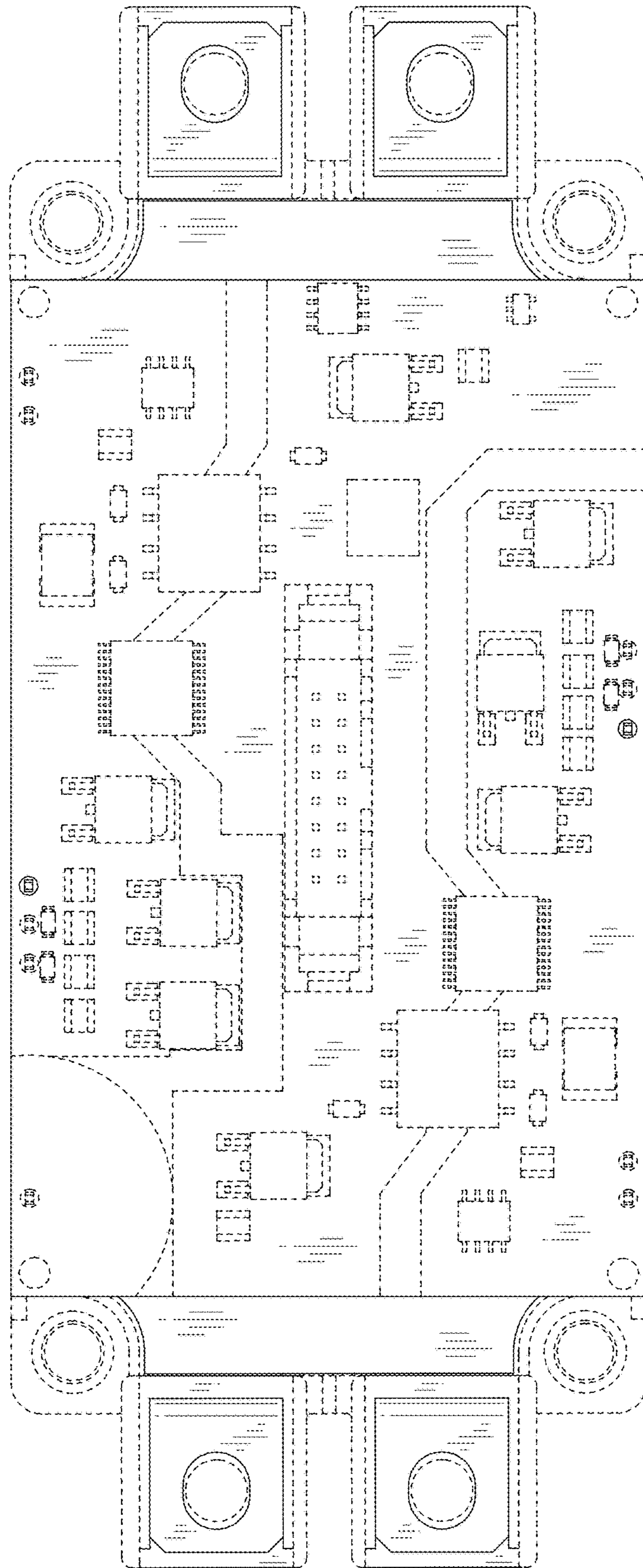


FIG. 4

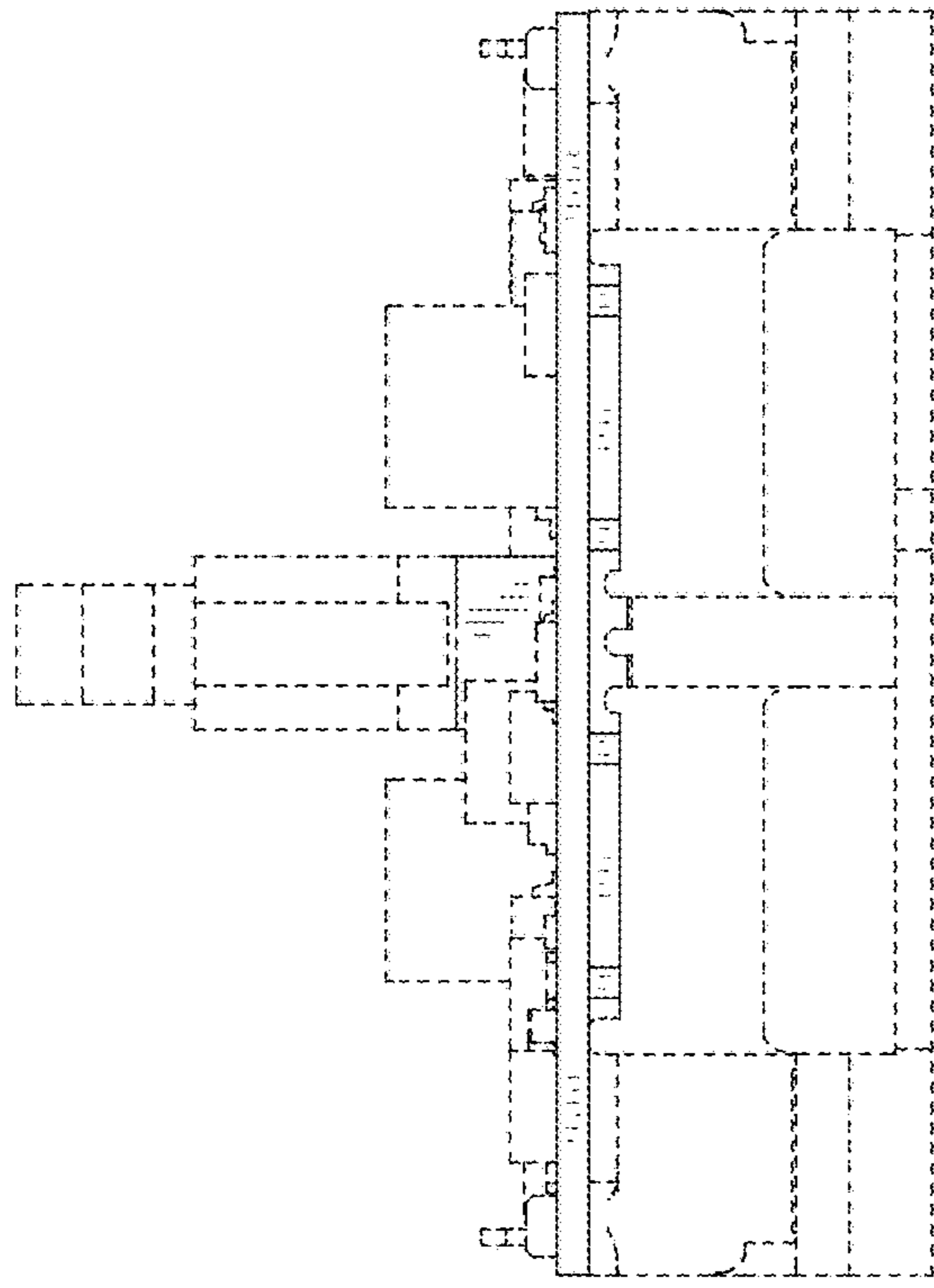


FIG.5

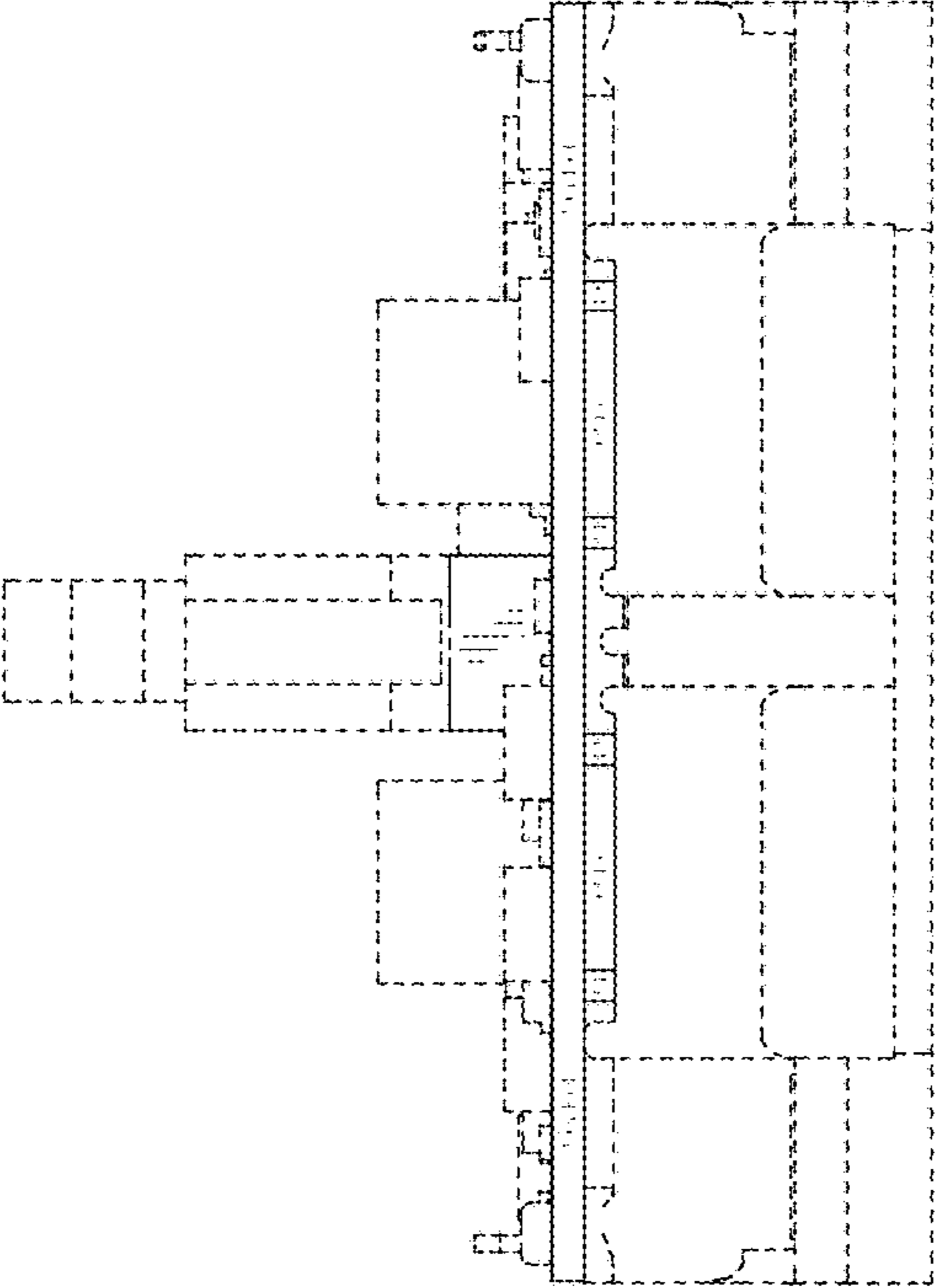


FIG.6



FIG. 7

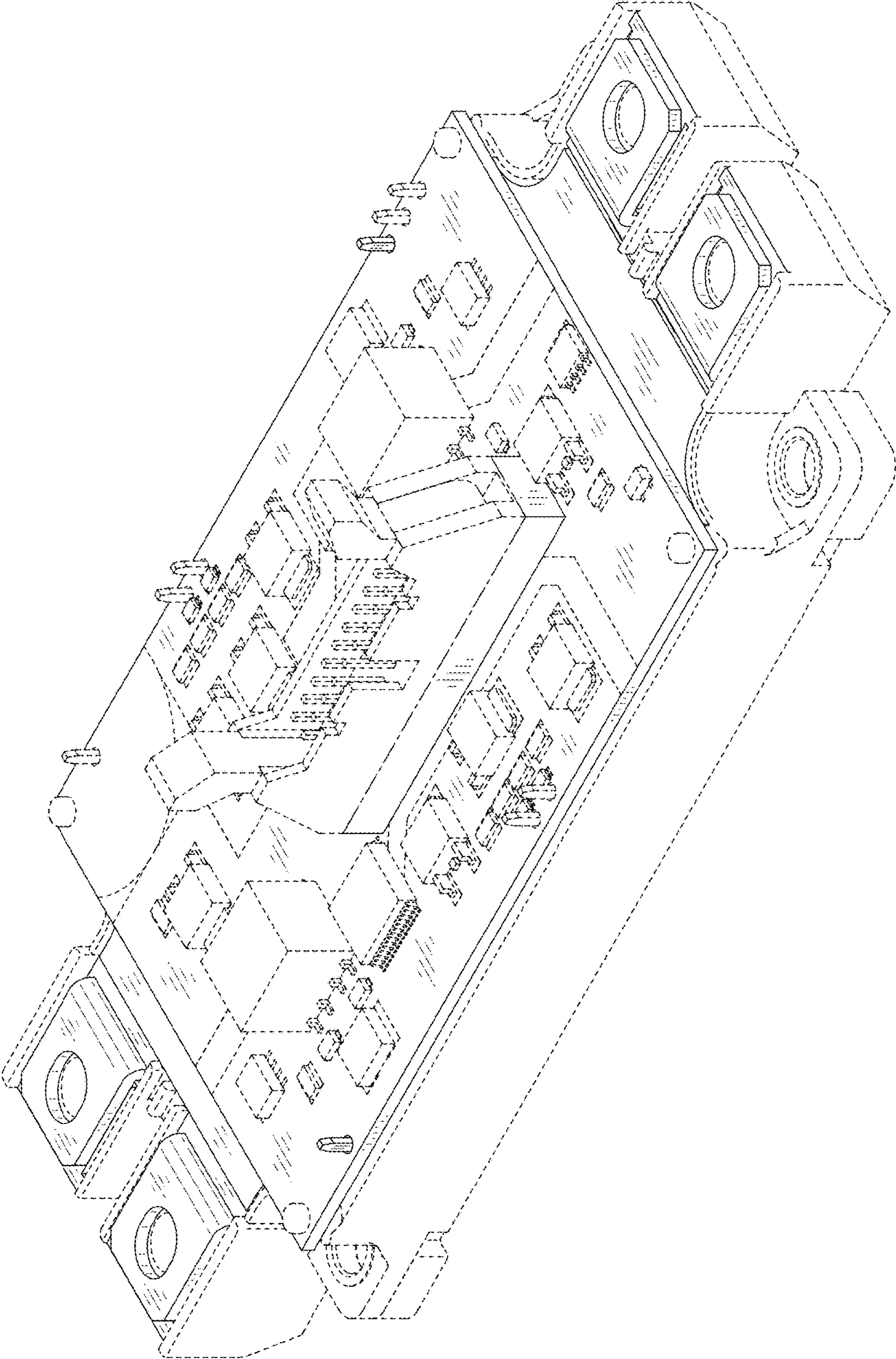


FIG.8

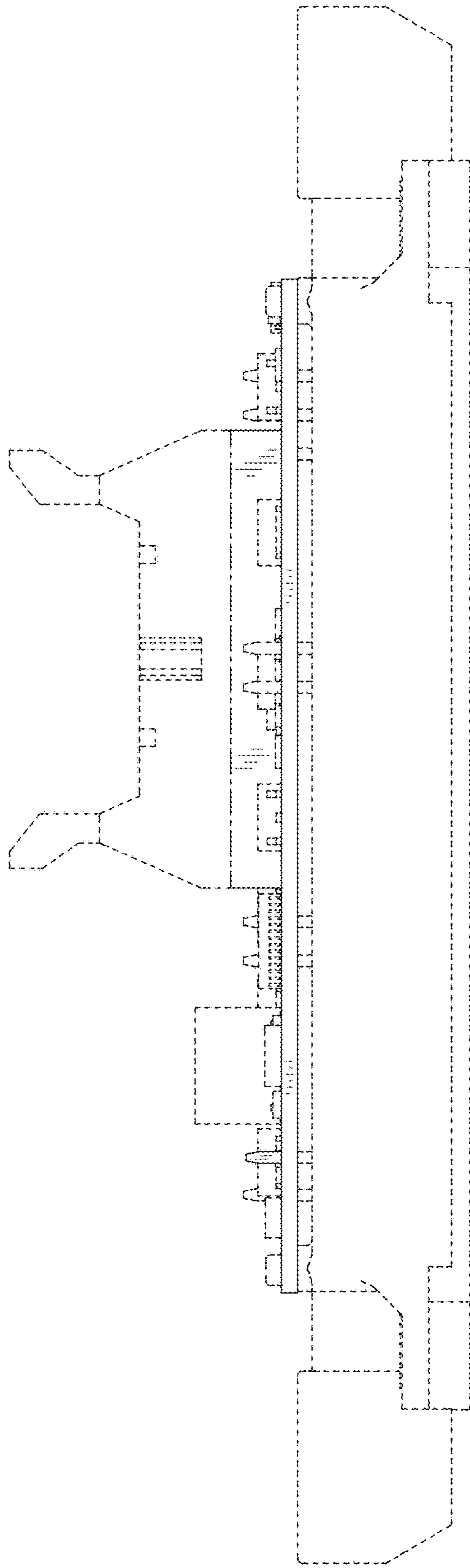
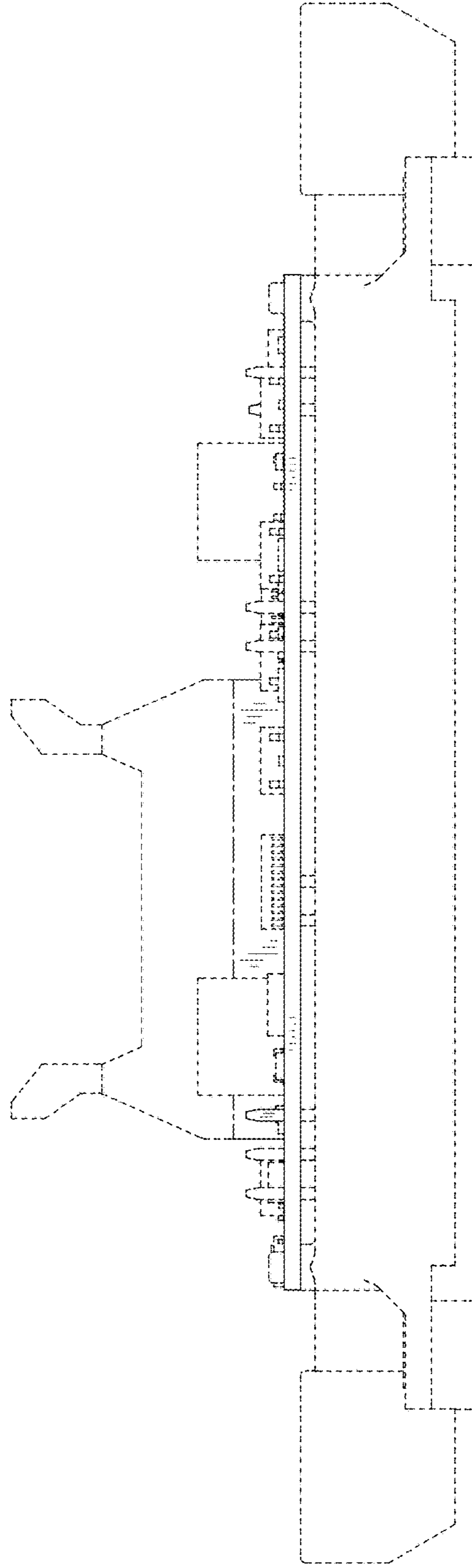


FIG. 9



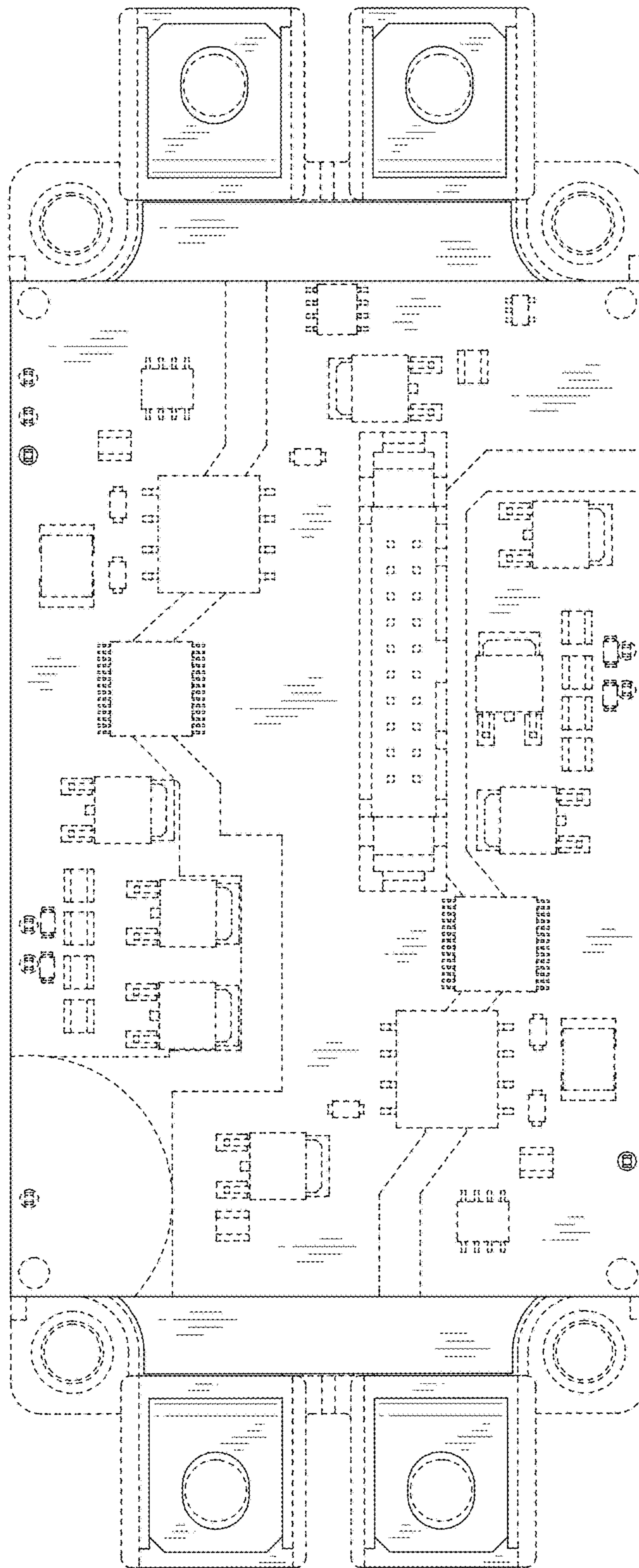


FIG.10

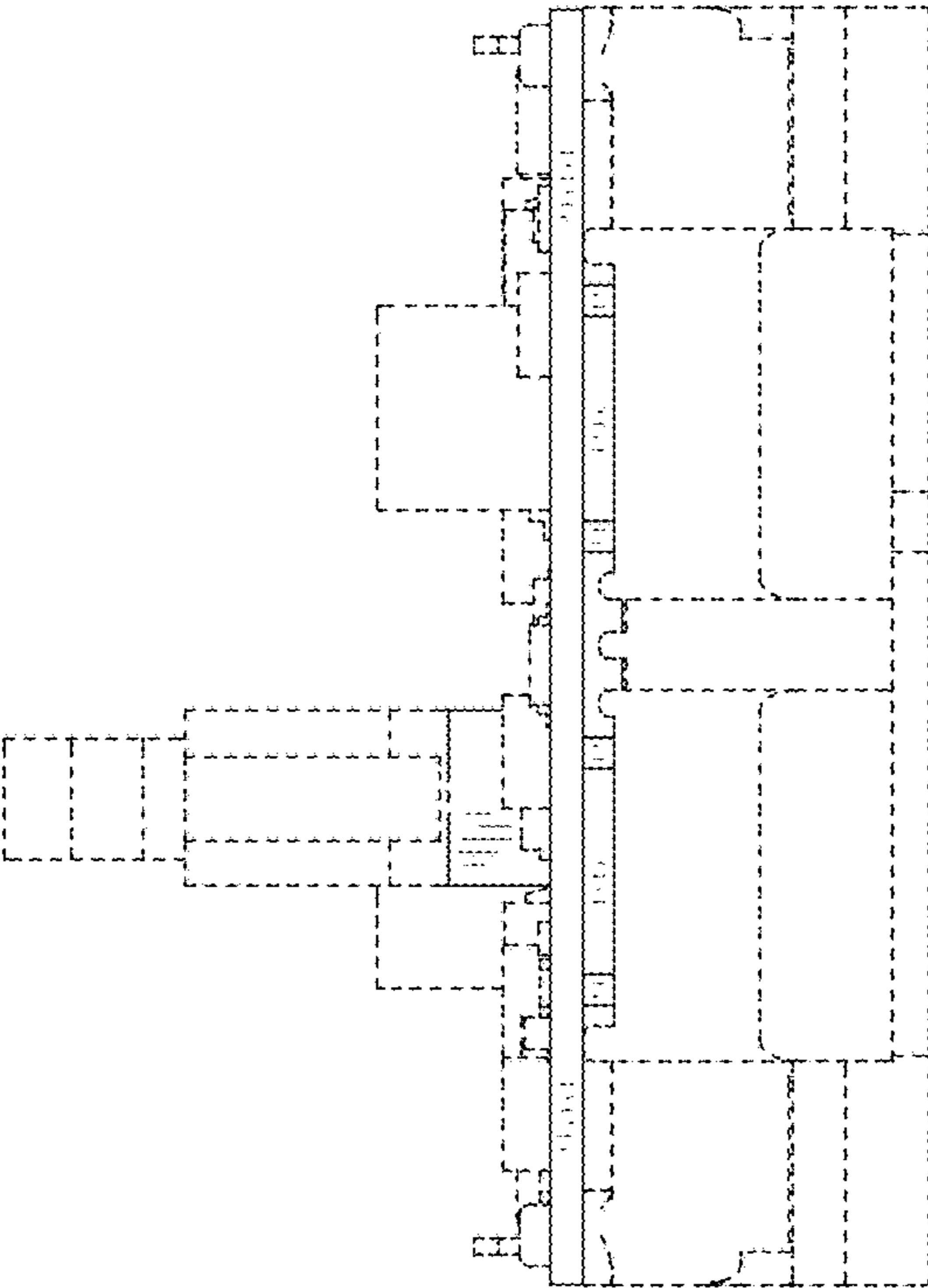


FIG.11

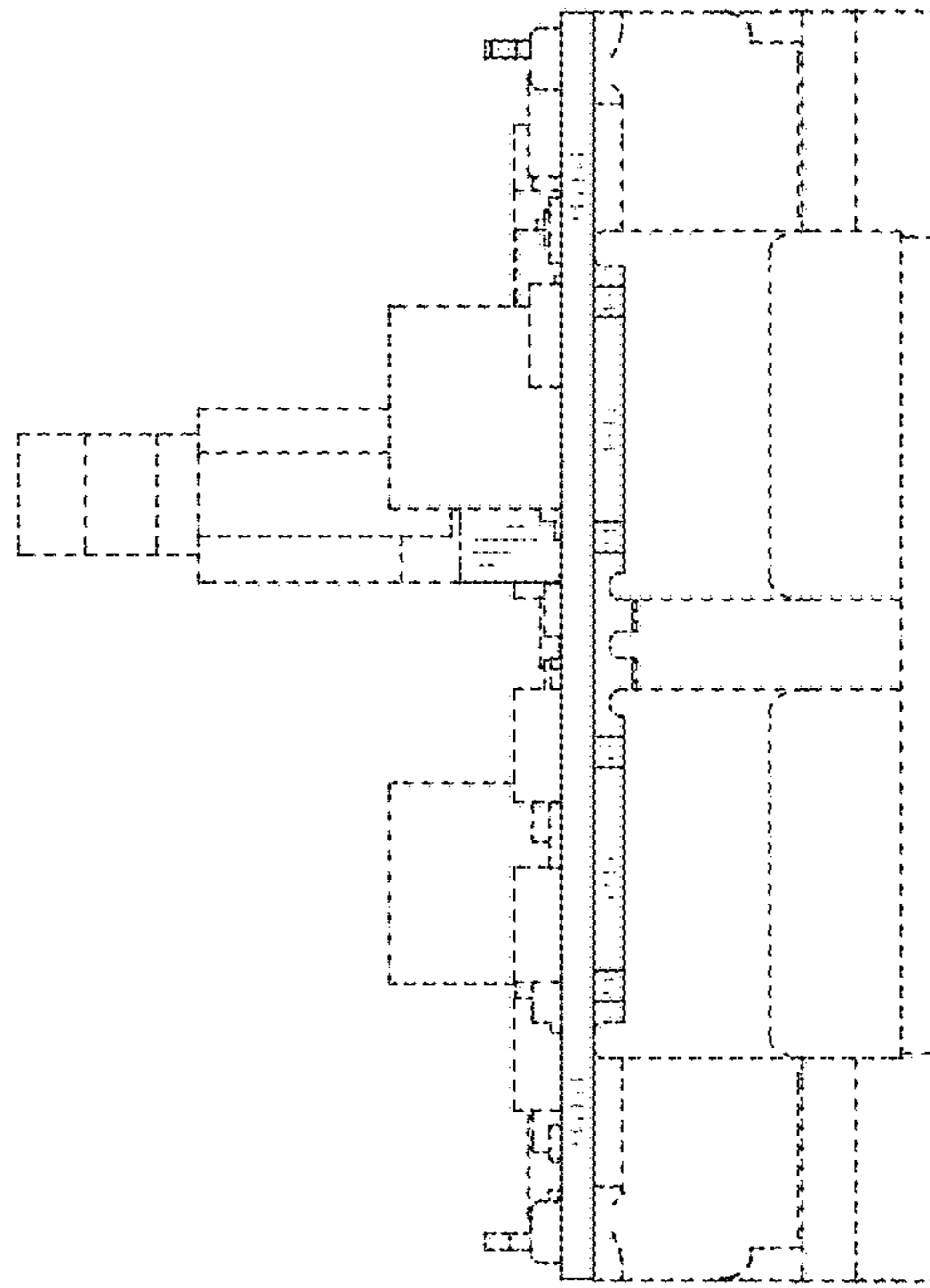


FIG.12